

1. TYPE LTC043ZM FS8
2. STRUCTURE NPN SILICON EPITAXIAL PLANAR DIGITAL TRANSISTOR
3. APPLICATIONS INVERTER, INTERFACE, DRIVER
4. ABSOLUTE MAXIMUM RATINGS [Ta=25°C]

SUPPLY VOLTAGE V_{CC} ... 50V

INPUT VOLTAGE V_{IN} ... 30V~-5V

COLLECTOR CURRENT $I_{C(max)}$... 100mA

CHARACTERISTICS OF
BUILT-IN TRANSISTOR

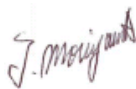
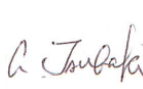

OUTPUT CURRENT I_O ... 100mA

POWER DISSIPATION P_D ... 150mW

EACH TERMINAL MOUNTED
ON A REFERENCE LAND

JUNCTION TEMPERATURE T_j ... 150°C

RANGE OF STORAGE TEMPERATURE T_{stg} ... -55~150°C

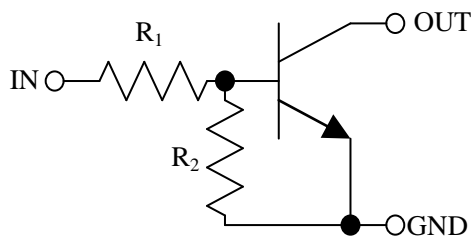
DESIGN	CHECK	APPROVAL	DATE : 20/APR/2011	SPECIFICATION No. : T837-LTC043ZM FS8
			REV. : 1	ROHM Co.,Ltd.

5. ELECTRICAL CHARACTERISTICS [Ta=25°C]

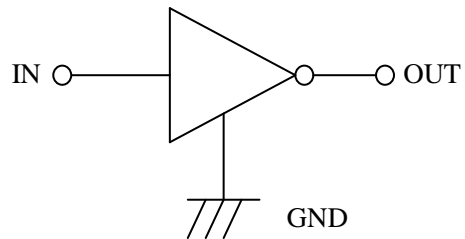
PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.
INPUT VOLTAGE	$V_{I(off)}$	$V_{CC}=5V / I_O=100\mu A$	-	-	0.5V
	$V_{I(on)}$	$V_O=0.3V / I_O=5mA$	1.1V	-	-
OUTPUT VOLTAGE	$V_{O(on)}$	$I_O=5mA / I_I=0.5mA$	-	0.05V	0.15V
INPUT CURRENT	I_I	$V_I=5V$	-	-	1.8mA
OUTPUT CURRENT	$I_{O(off)}$	$V_{CC}=50V / V_I=0V$	-	-	500nA
DC CURRENT GAIN	G_I	$V_O=10V / I_O=5mA$	80	-	-
TRANSITION FREQUENCY *	f_T	$V_{CE}=10V / I_E=-5mA$ $f=100MHz$	-	250MHz	-
INPUT RESISTANCE	R_I		3.29k Ω	4.7k Ω	6.11k Ω
RESISTANCE RATIO	R_2/R_1		8	10	12

*CHARACTERISTICS OF BUILT-IN TRANSISTOR

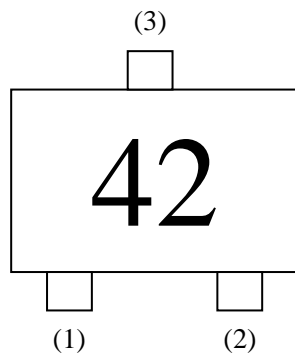
6. INTERNAL CIRCUIT



$R_1=4.7k\Omega$
 $R_2=47k\Omega$



7. MARKING



“ 42 ” MEAN LTC043ZM FS8

(1) IN
(2) GND
(3) OUT